



SamHop Microelectronics Corp.

STM7822

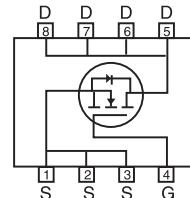
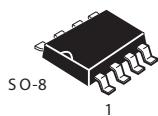
Arp,20 2005 ver1.1

## N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DSON</sub> (mΩ) Max
25V	14A	6.5 @ V <sub>GS</sub> = 10V
		7.5 @ V <sub>GS</sub> = 4.5V

### FEATURES

- Super high dense cell design for low R<sub>DSON</sub>.
- Rugged and reliable.
- Surface Mount Package.



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage Rating	V <sub>spike</sub> <sup>d</sup>	30	V
Drain-Source Voltage	V <sub>DS</sub>	25	V
Gate-Source Voltage	V <sub>GS</sub>	±16	V
Drain Current-Continuous <sup>a</sup> @ T <sub>c</sub> =25C° -Pulsed <sup>b</sup>	I <sub>D</sub>	14	A
	I <sub>DM</sub>	56	A
Drain-Source Diode Forward Current <sup>a</sup>	I <sub>S</sub>	14	A
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	2.5	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient <sup>a</sup>	R <sub>θJA</sub>	50	°C/W
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# STM7822

ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	25			V
Zero Gate Voltage Drain Current	$I_{\text{DS}}$	$V_{\text{DS}}=20\text{V}, V_{\text{GS}}=0\text{V}$		1		$\mu\text{A}$
Gate-Body Leakage	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 16\text{V}, V_{\text{DS}}=0\text{V}$		$\pm 100$		nA
<b>ON CHARACTERISTICS <sup>b</sup></b>						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	0.7	1.0		V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=14\text{A}$			6.5	m ohm
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=10\text{A}$			7.5	m ohm
On-State Drain Current	$I_{\text{D}(\text{ON})}$	$V_{\text{DS}}=10\text{V}, V_{\text{GS}}=10\text{V}$	10			A
Forward Transconductance	$g_{\text{F}}$	$V_{\text{DS}}=10\text{V}, I_{\text{D}}=14\text{A}$		20		S
<b>DYNAMIC CHARACTERISTICS <sup>c</sup></b>						
Input Capacitance	$C_{\text{ISS}}$	$V_{\text{DS}}=16\text{V}, V_{\text{GS}}=0\text{V}$ $f=1.0\text{MHz}$		3725		pF
Output Capacitance	$C_{\text{OSS}}$			663		pF
Reverse Transfer Capacitance	$C_{\text{RSS}}$			494		pF
<b>SWITCHING CHARACTERISTICS <sup>c</sup></b>						
Turn-On Delay Time	$t_{\text{D}(\text{ON})}$	$V_{\text{DD}}=16\text{V},$ $I_{\text{D}}=14\text{A},$ $V_{\text{GS}}=5\text{V},$ $R_{\text{GEN}}=6 \text{ ohm}$		18.1		ns
Rise Time	$t_{\text{r}}$			6.5		ns
Turn-Off Delay Time	$t_{\text{D}(\text{OFF})}$			26.8		ns
Fall Time	$t_{\text{f}}$			17.1		ns
Total Gate Charge	$Q_g$	$V_{\text{DS}}=16\text{V}, I_{\text{D}}=14\text{A}, V_{\text{GS}}=10\text{V}$		87.4		nC
		$V_{\text{DS}}=16\text{V}, I_{\text{D}}=14\text{A}, V_{\text{GS}}=5\text{V}$		45.2		nC
Gate-Source Charge	$Q_{\text{gs}}$	$V_{\text{DS}}=16\text{V}, I_{\text{D}}=14\text{A},$ $V_{\text{GS}}=5\text{V}$		10		nC
Gate-Drain Charge	$Q_{\text{gd}}$			14.3		nC

# STM7822

ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS <sup>b</sup>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 14A$		0.84	1.2	V

## Notes

- a. Surface Mounted on FR4 Board,  $t \leq 10\text{ sec}$ .
- b. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
- c. Guaranteed by design, not subject to production testing.
- d. Guaranteed when external  $R_g=6\text{ ohm}$  and  $t_f < t_{f\max}$

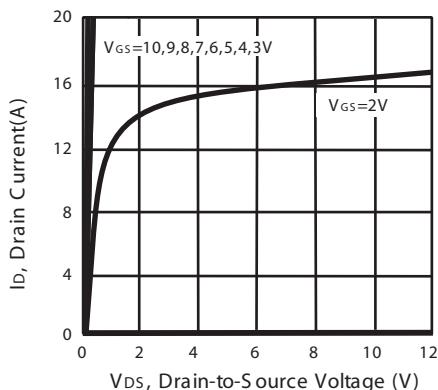


Figure 1. Output Characteristics

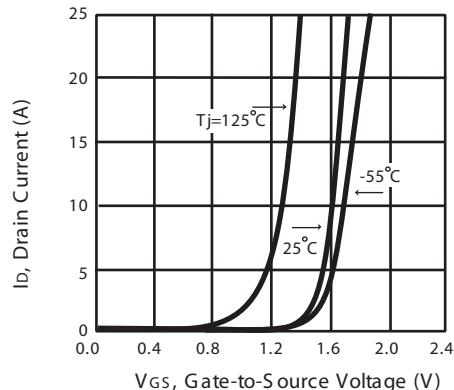


Figure 2. Transfer Characteristics

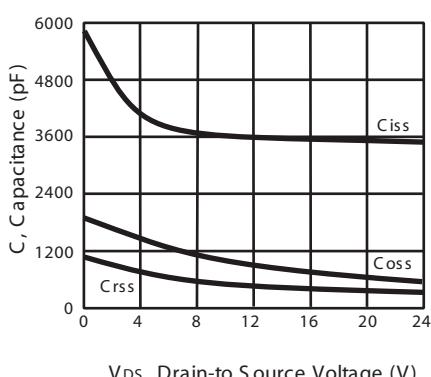


Figure 3. Capacitance

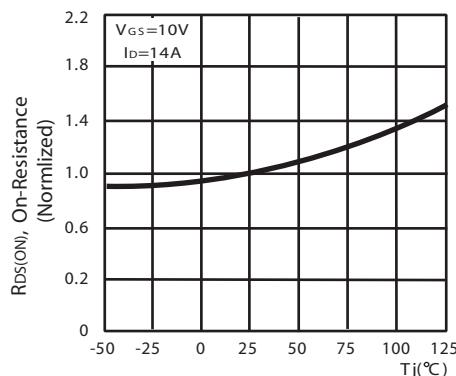


Figure 4. On-Resistance Variation with Temperature

# STM7822

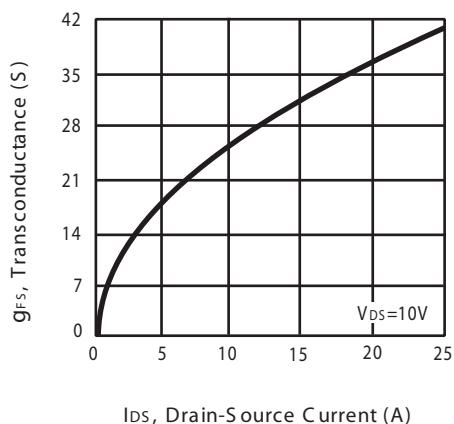
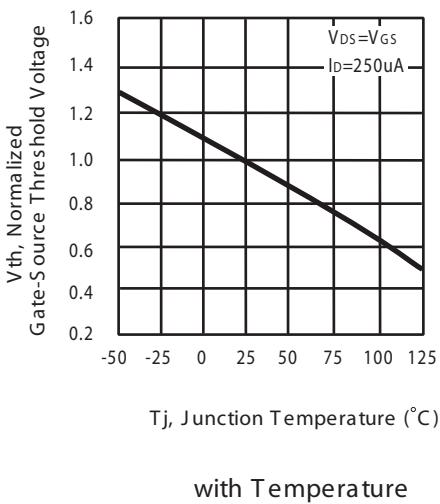


Figure 7. Transconductance Variation with Drain Current

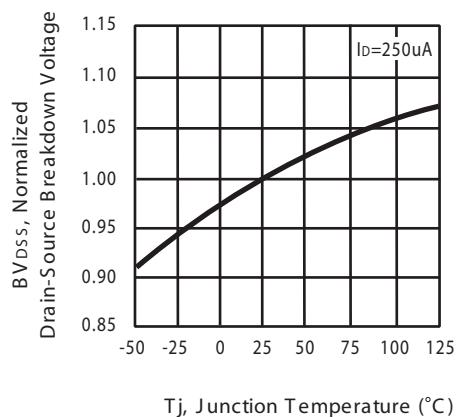


Figure 6. Breakdown Voltage Variation with Temperature

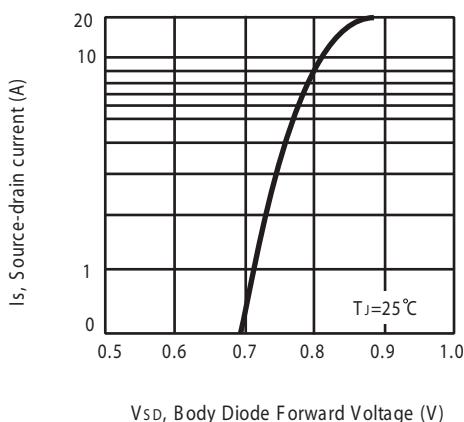


Figure 8. Body Diode Forward Voltage Variation with Source Current

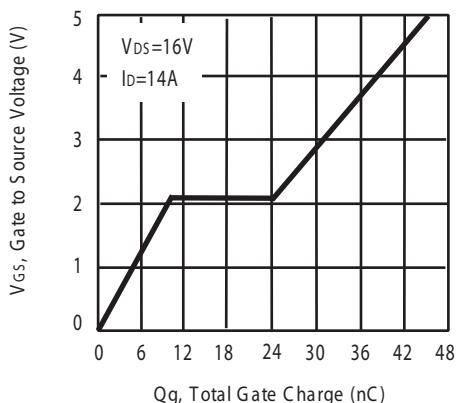


Figure 9. Gate Charge

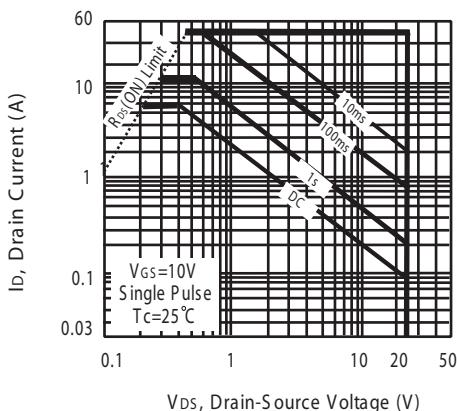


Figure 10. Maximum Safe Operating Area

# STM7822

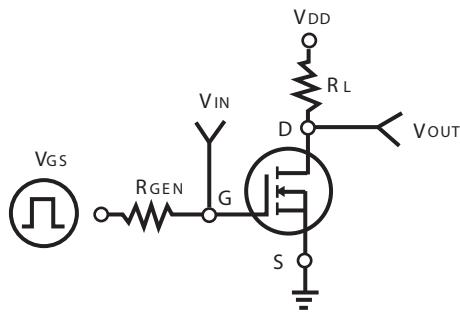


Figure 11. S switching Test Circuit

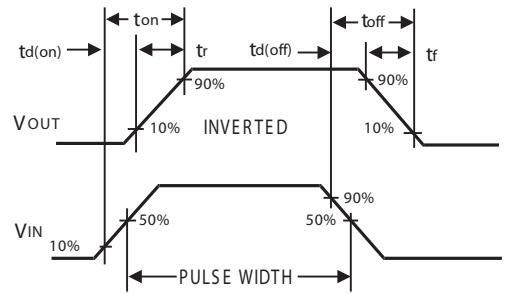


Figure 12. S switching Waveforms

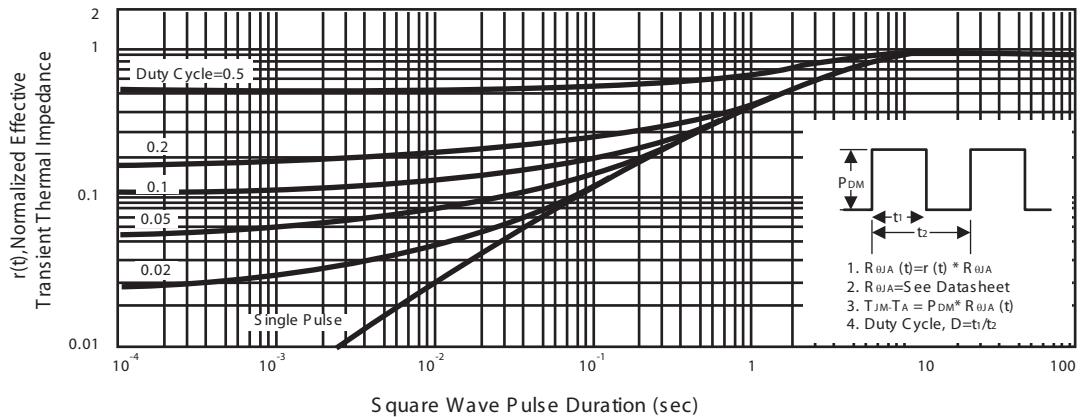
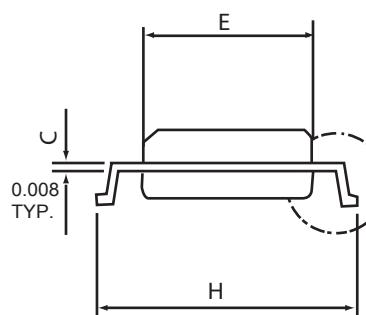
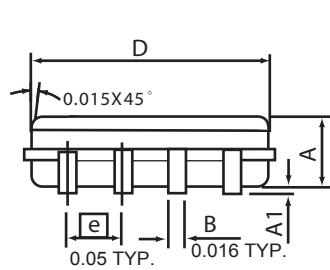
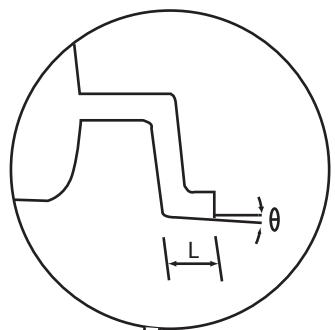
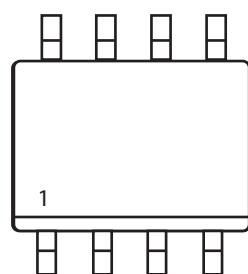


Figure 13. Normalized Thermal Transient Impedance Curve

# STM7822

## PACKAGE OUTLINE DIMENSIONS

SO-8

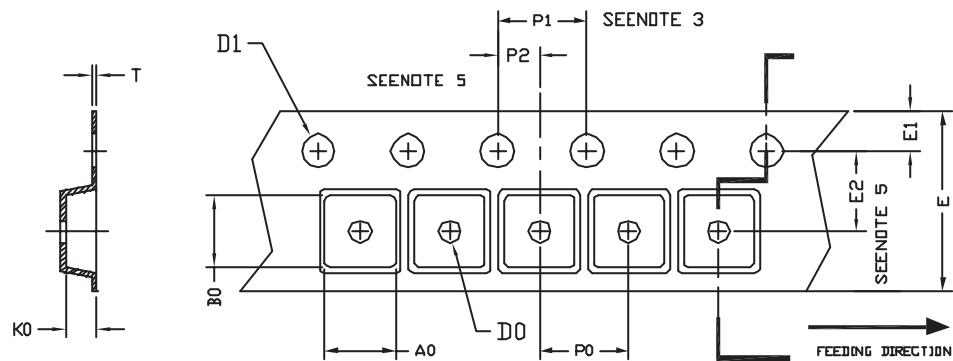


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	4.98	0.189	0.196
E	3.81	3.99	0.150	0.157
H	5.79	6.20	0.228	0.244
L	0.41	1.27	0.016	0.050
$\theta$	$0^\circ$	$8^\circ$	$0^\circ$	$8^\circ$

# STM7822

## SO-8 Tape and Reel Data

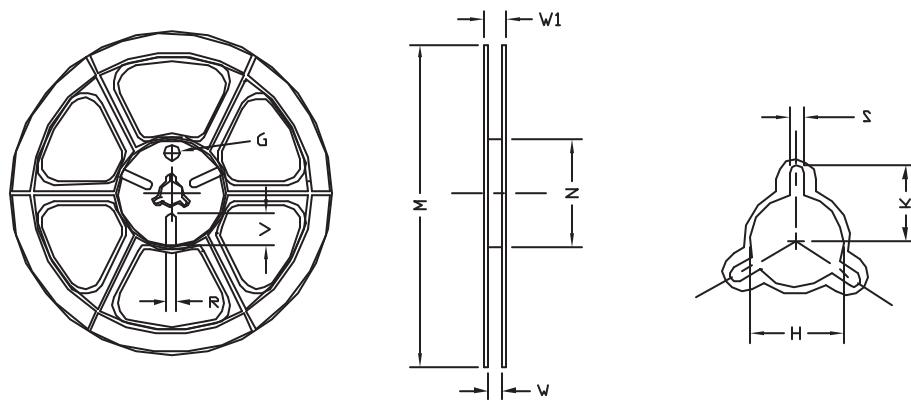
### SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.40	5.20	2.10	$\phi 1.5$ (MIN)	$\phi 1.5$ $+ 0.1$ $- 0.0$	12.0 $\pm 0.3$	1.75	5.5 $\pm 0.05$	8.0	4.0	$2.0$ $\pm 0.05$	$0.3$ $\pm 0.05$

### SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	$\phi 330$	330 $\pm 1$	62 $\pm 1.5$	12.4 $+ 0.2$	16.8 $- 0.4$	$\phi 12.75$ $+ 0.15$	---	2.0 $\pm 0.15$	---	---	---